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			Application Number	New- 10 / 827 380	
			Filing Date	Concurrently Herewith	
			First Named Inventor	Alon Regev	
			Prior Art Unit	2818	
			Prior Examiner Name	L. Tran	
Sheet	1	of	1	Attorney Docket Number	M4065.0579/P579-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
UAT	AA	6,101,115	08/2000	Ross	
UAT	AB	6,240,001 B1	05/2001	Ross	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
UAT	AD	"Half-V _{DD} Bit-Line Sensing Scheme in CMOS DRAM's," Nicky Chau-Chun Lu et al., IEEE Journal of Solid-State Circuits, Vol. SC-19, No. 4, August 1984, pp. 451-454			
UAT	AE	"A 256M DRAM with Simplified Register Control for Low Power Self Refresh and Rapid Burn-in," Seung-Moon Yoo et al., 1994 Symposium on VLSI Circuits Digest of Technical Papers, pp. 85 and 86			
UAT	AF	"Automatic Voltage-Swing Reduction (AVR) Scheme for Ultra Low Power DRAMs," Masaki Tsukude et al., 1994 Symposium on VLSI Circuits Digest of Technical Papers, pp. 87 and 88			
UAT	AG	"A 250mV Bit-Line Swing Scheme for a 1V 4Gb DRAM," T. Inaba et al., 1995 Symposium on VLSI Circuits Digest of Technical Papers, pp. 99 and 100			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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